

## Darlington Complementary Silicon Power Transistors

... designed for general purpose and low speed switching applications.

- High DC Current Gain —  $h_{FE} = 2500$  (typ.) at  $I_C = 4.0$
- Collector-Emitter Sustaining Voltage at 100 mAdc  
 $V_{CEO(sus)} = 80$  Vdc (min.) — BDX33B, 34B  
 $100$  Vdc (min.) — BDX33C, 34C
- Low Collector-Emitter Saturation Voltage  
 $V_{CE(sat)} = 2.5$  Vdc (max.) at  $I_C = 3.0$  Adc — BDX33B, 33C/34B, 34C
- Monolithic Construction with Build-In Base-Emitter Shunt resistors
- TO-220AB Compact Package

### MAXIMUM RATINGS

Rating	Symbol	BDX33B BDX34B	BDX33C BDX34C	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	100	Vdc
Collector-Base Voltage	$V_{CB}$	80	100	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0		Vdc
Collector Current — Continuous Peak	$I_C$	10 15		Adc
Base Current	$I_B$	0.25		Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	70 0.56		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{Stg}$	-65 to +150		$^\circ\text{C}$

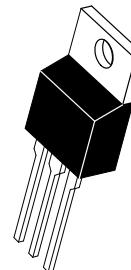
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.78	$^\circ\text{C}/\text{W}$

**NPN**  
**BDX33B**  
**BDX33C\***  
**PNP**  
**BDX34B**  
**BDX34C\***

\*Motorola Preferred Device

**DARLINGTON  
10 AMPERE  
COMPLEMENTARY  
SILICON  
POWER TRANSISTORS  
80–100 VOLTS  
70 WATTS**



CASE 221A-06  
TO-220AB

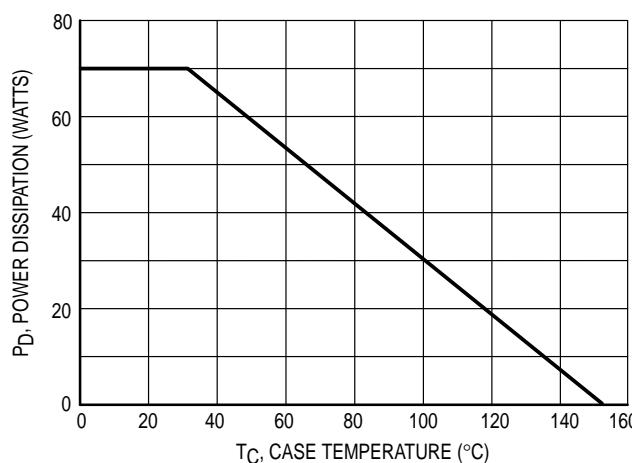


Figure 1. Power Derating

Preferred devices are Motorola recommended choices for future use and best overall value.

REV 7

**BDX33B BDX33C BDX34B BDX34C**
**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

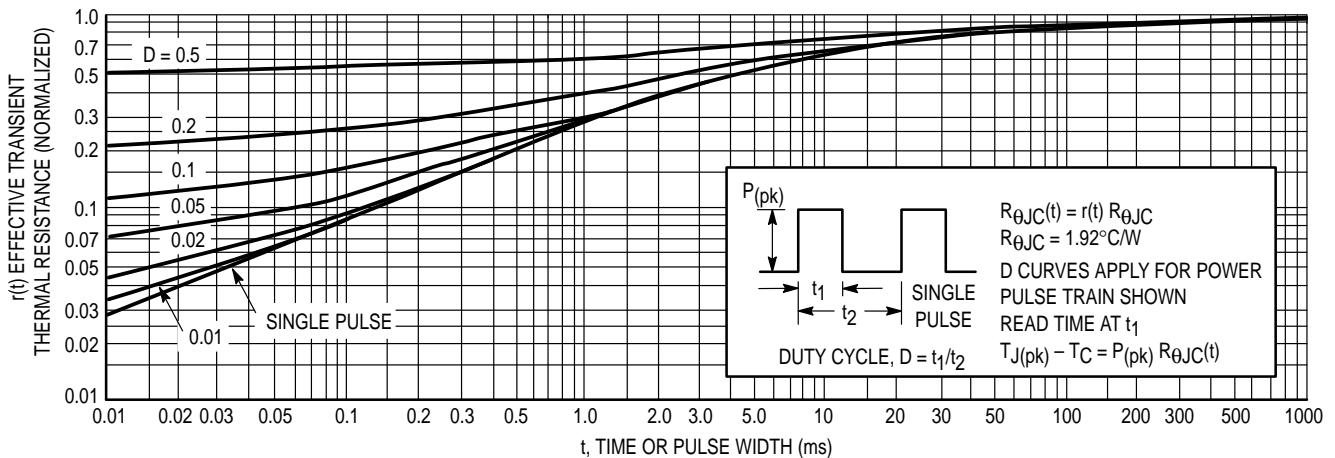
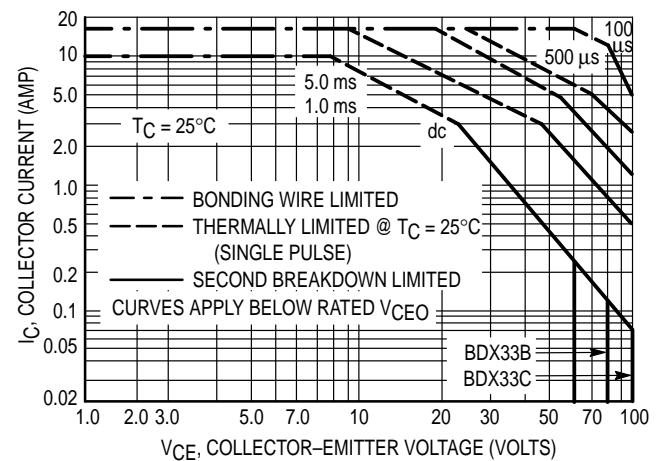
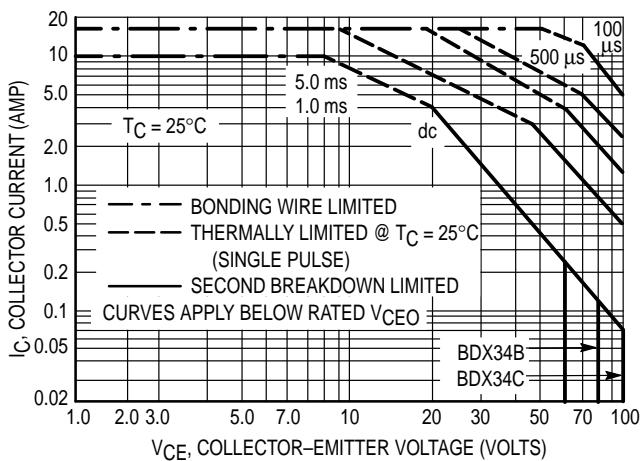
Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Sustaining Voltage <sup>1</sup> ( $I_C = 100 \text{ mA}_\text{dc}$ , $I_B = 0$ ) BDX33B/BDX34B BDX33C/BDX34C	$V_{CEO(\text{sus})}$	80 100	— —	Vdc
Collector-Emitter Sustaining Voltage <sup>1</sup> ( $I_C = 100 \text{ mA}_\text{dc}$ , $I_B = 0$ , $R_{BE} = 100$ ) BDX33B/BDX34B BDX33C/BDX34C	$V_{CER(\text{sus})}$	80 100	— —	Vdc
Collector-Emitter Sustaining Voltage <sup>1</sup> ( $I_C = 100 \text{ mA}_\text{dc}$ , $I_B = 0$ , $V_{BE} = 1.5 \text{ Vdc}$ ) BDX33B/BDX34B BDX33C/BDX34C	$V_{CEX(\text{sus})}$	80 100	— —	Vdc
Collector Cutoff Current ( $V_{CE} = 1/2$ rated $V_{CEO}$ , $I_B = 0$ ) $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_{CEO}$	— —	0.5 10	$\text{mA}_\text{dc}$
Collector Cutoff Current ( $V_{CB} = \text{rated } V_{CBO}$ , $I_E = 0$ ) $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_{CBO}$	— —	1.0 5.0	$\text{mA}_\text{dc}$
Emitter Cutoff Current ( $V_{BE} = 5.0 \text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	—	10	$\text{mA}_\text{dc}$

**ON CHARACTERISTICS**

DC Current Gain <sup>1</sup> ( $I_C = 3.0 \text{ Adc}$ , $V_{CE} = 3.0 \text{ Vdc}$ ) BDX33B, 33C/34B, 34C	$h_{FE}$	750	—	—
Collector-Emitter Saturation Voltage ( $I_C = 3.0 \text{ Adc}$ , $I_B = 6.0 \text{ mA}_\text{dc}$ ) BDX33B, 33C/34B, 34C	$V_{CE(\text{sat})}$	—	2.5	Vdc
Base-Emitter On Voltage ( $I_C = 3.0 \text{ Adc}$ , $V_{CE} = 3.0 \text{ Vdc}$ ) BDX33B, 33C/34B, 34C	$V_{BE(\text{on})}$	—	2.5	Vdc
Diode Forward Voltage ( $I_C = 8.0 \text{ Adc}$ )	$V_F$	—	4.0	Vdc

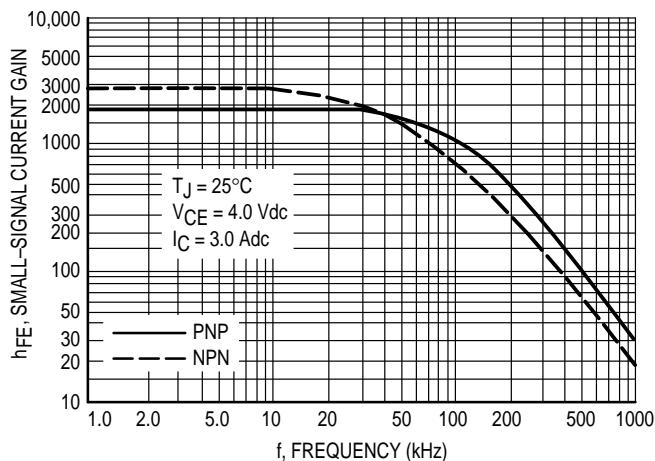
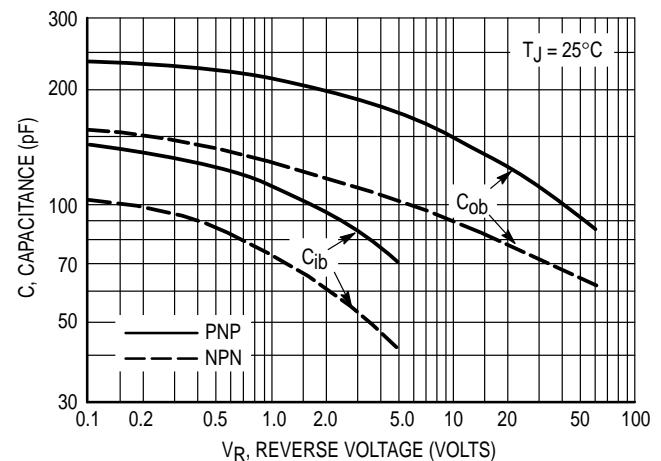
<sup>1</sup> Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

<sup>2</sup> Pulse Test non repetitive: Pulse Width = 0.25 s.


**Figure 1. Thermal Response**

**Figure 2. Active-Region Safe Operating Area**

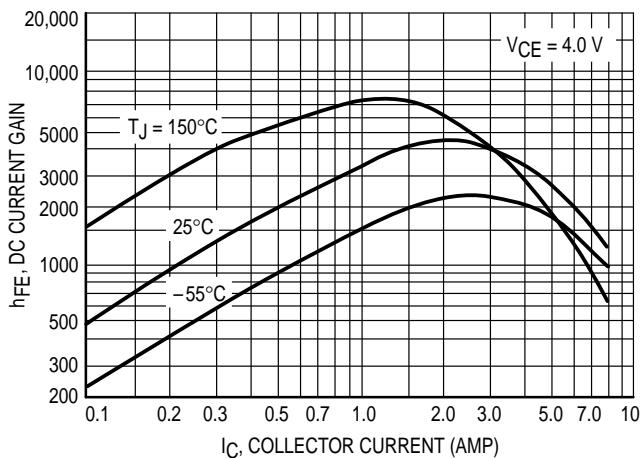
There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Fig. 3 is based on

$T_J(pk) = 150^{\circ}\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_J(pk) = 150^{\circ}\text{C}$ .  $T_J(pk)$  may be calculated from the data in Fig. . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

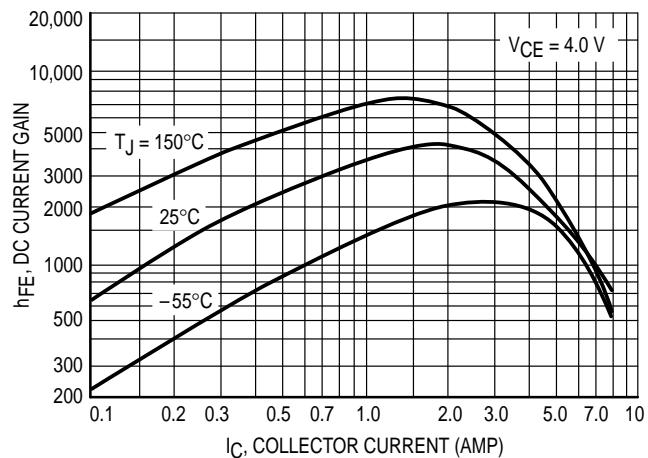

**Figure 3. Small-Signal Current Gain**

**Figure 4. Capacitance**

## **BDX33B BDX33C BDX34B BDX34C**

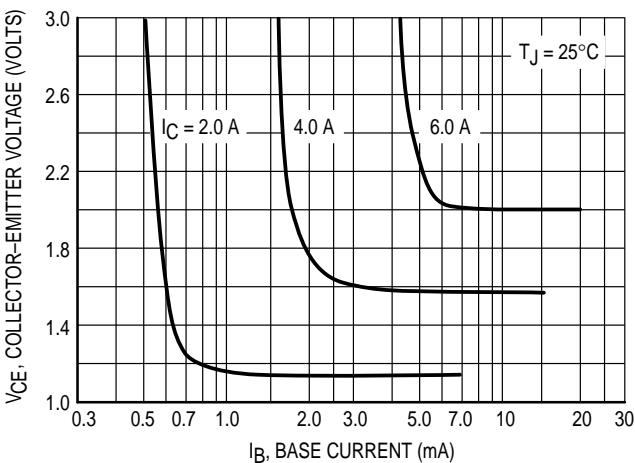
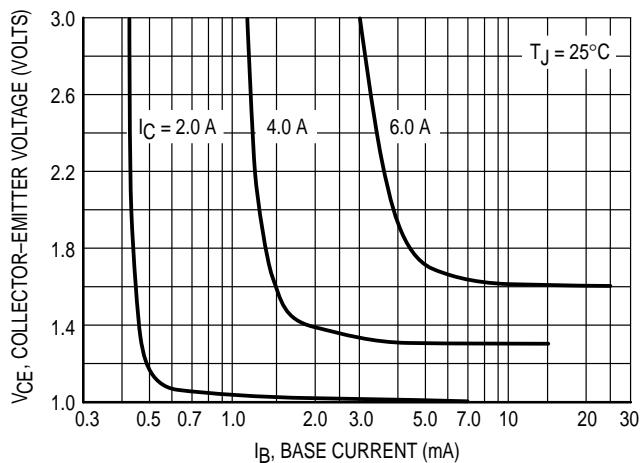
**NPN**  
**BDX33B, 33C**



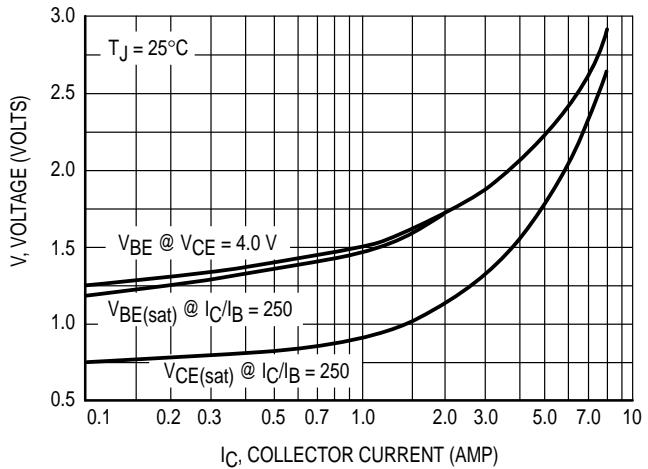
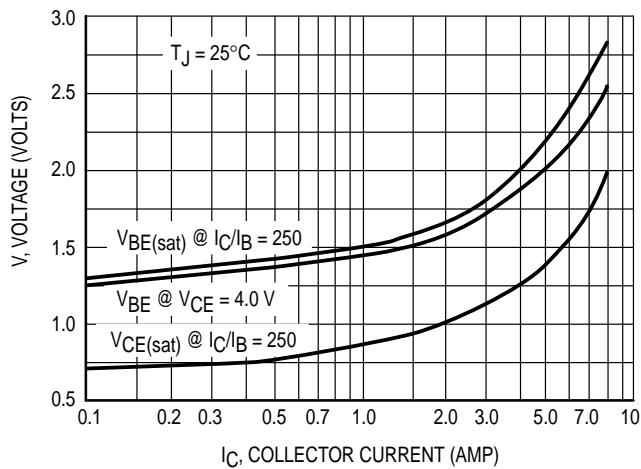
**PNP**  
**BDX34B, 34C**



**Figure 5. DC Current Gain**

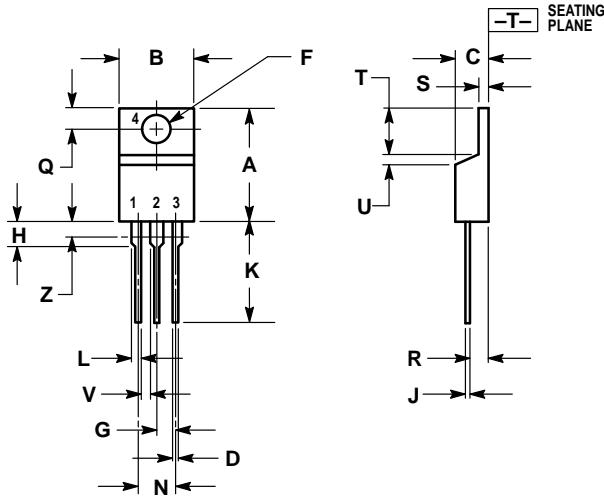


**Figure 6. Collector Saturation Region**



**Figure 7. "On" Voltages**

## PACKAGE DIMENSIONS



NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.  
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

STYLE 1:  
 PIN 1. BASE  
 2. COLLECTOR  
 3. Emitter  
 4. COLLECTOR

CASE 221A-06  
 TO-220AB  
 ISSUE Y

## **BDX33B BDX33C BDX34B BDX34C**

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**BDX33B/D**

